

Fig. 1

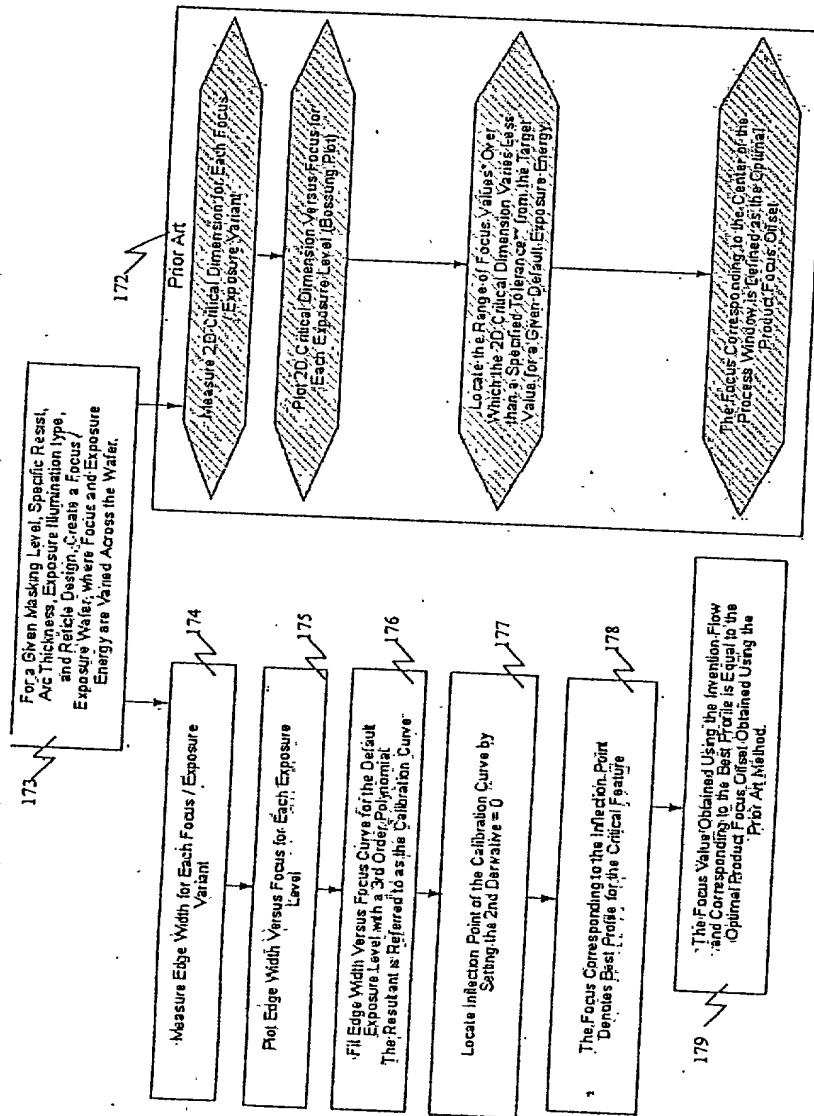


Fig. 1A

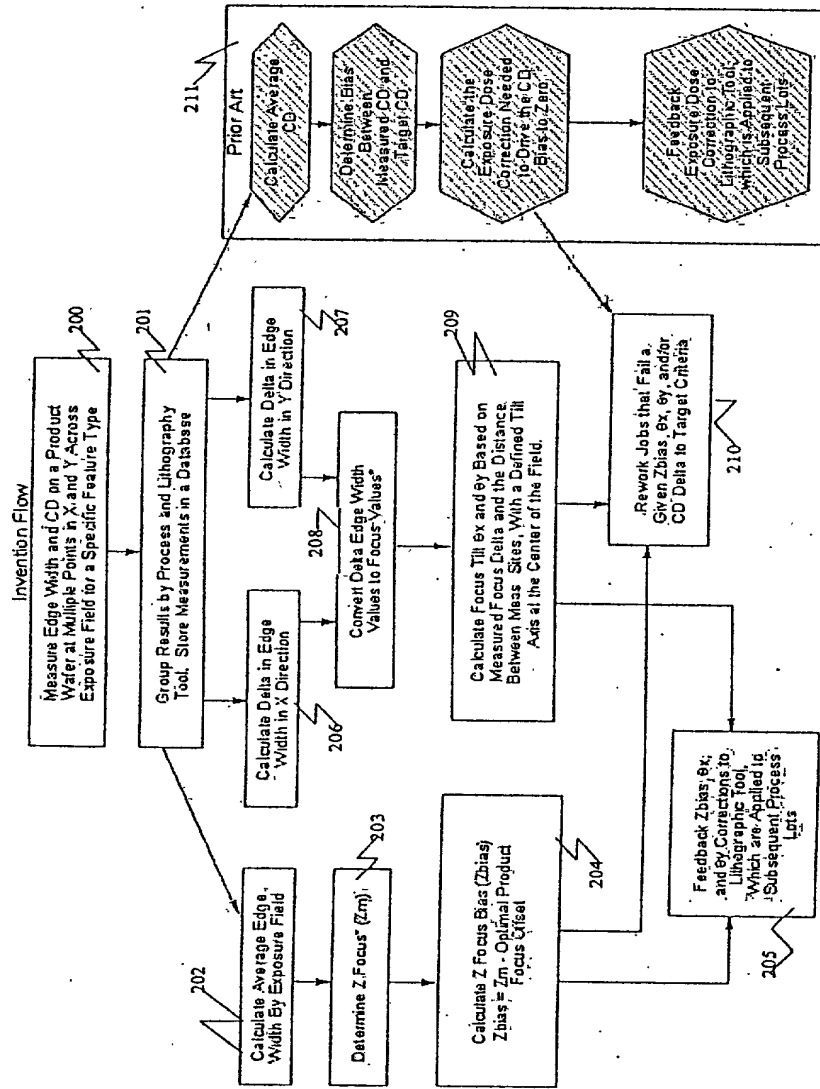


Fig. 1B

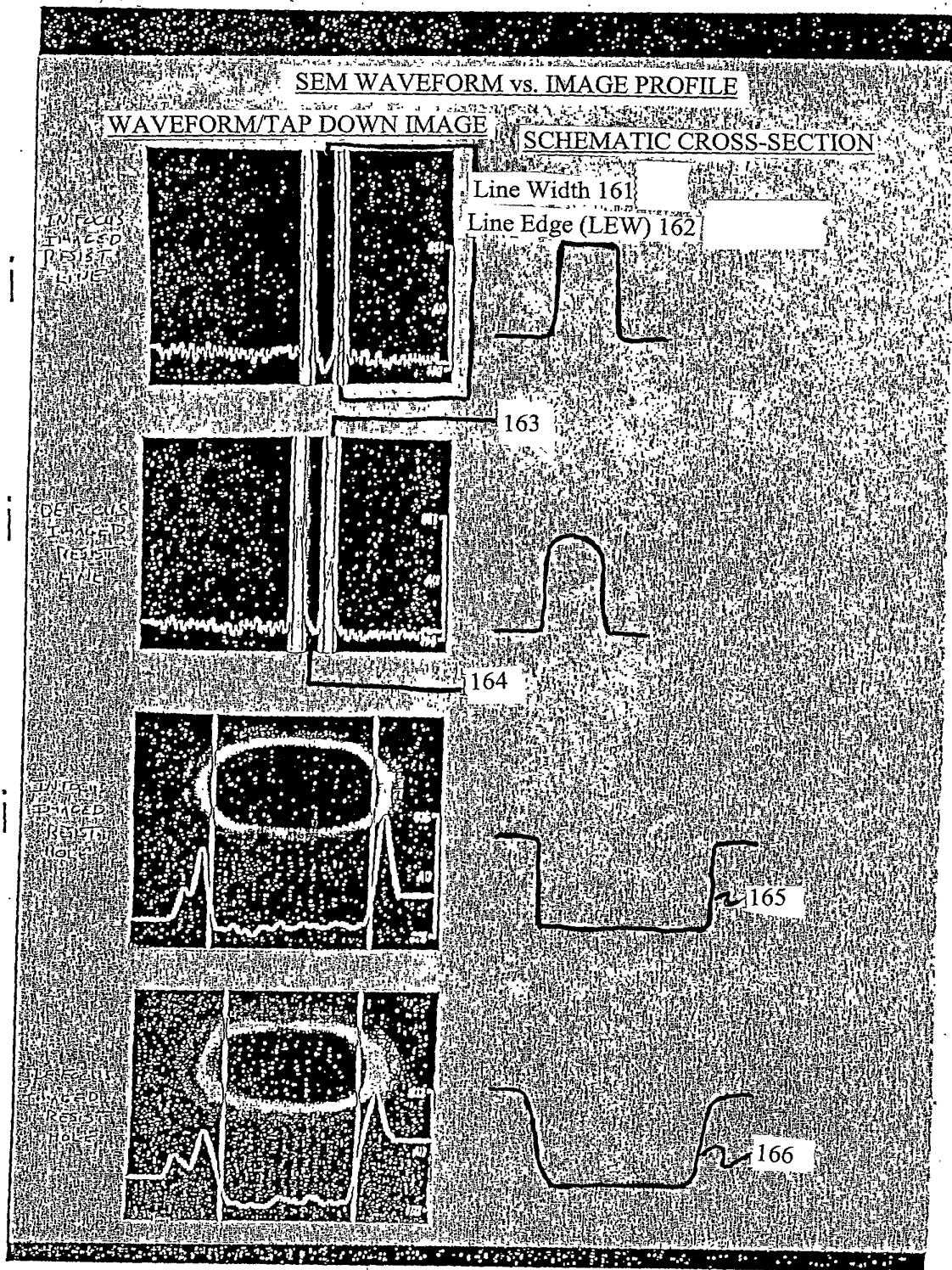


Fig. 1C

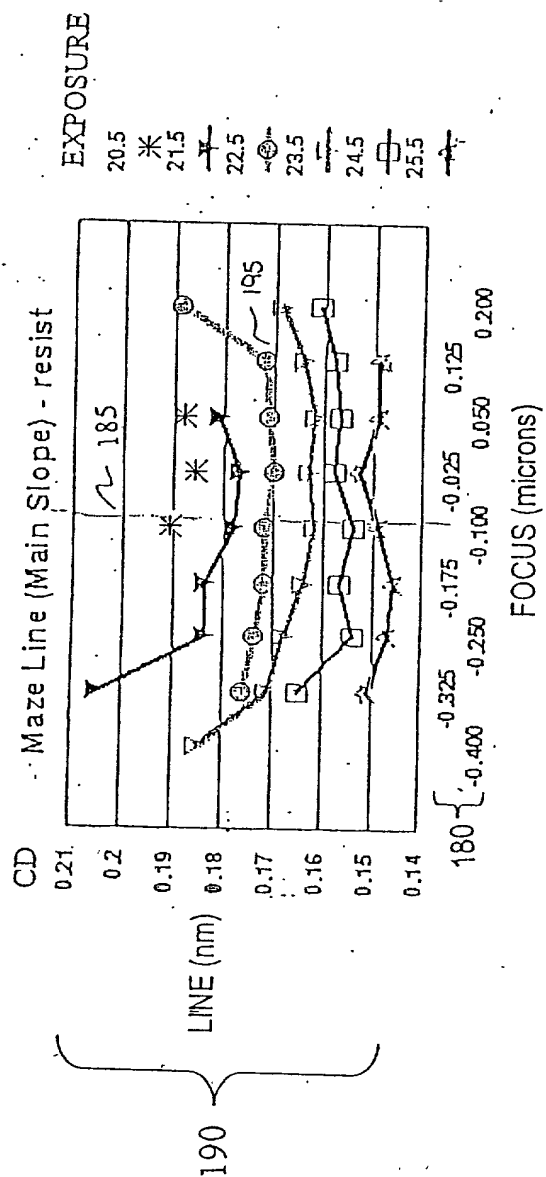


Fig. 1D

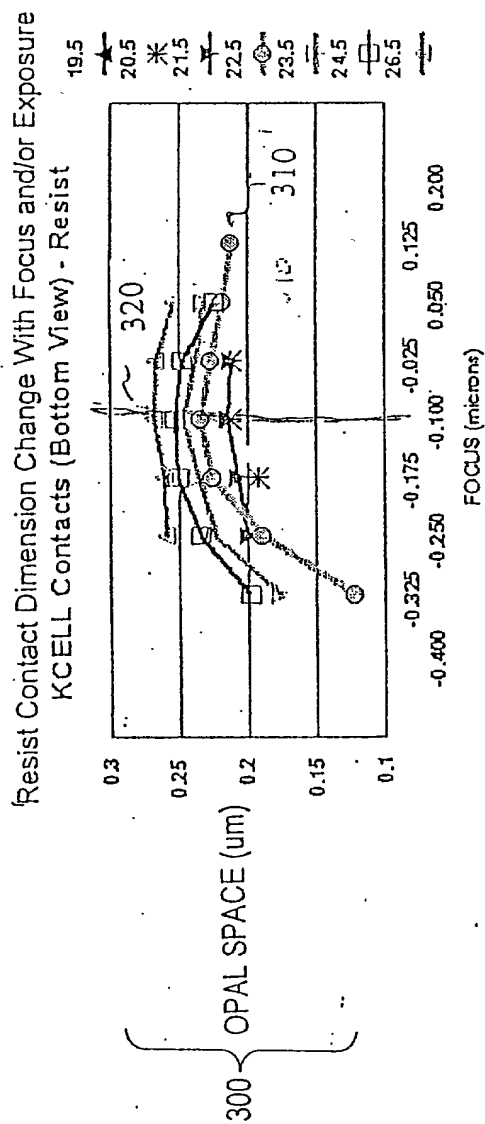


Fig. 2

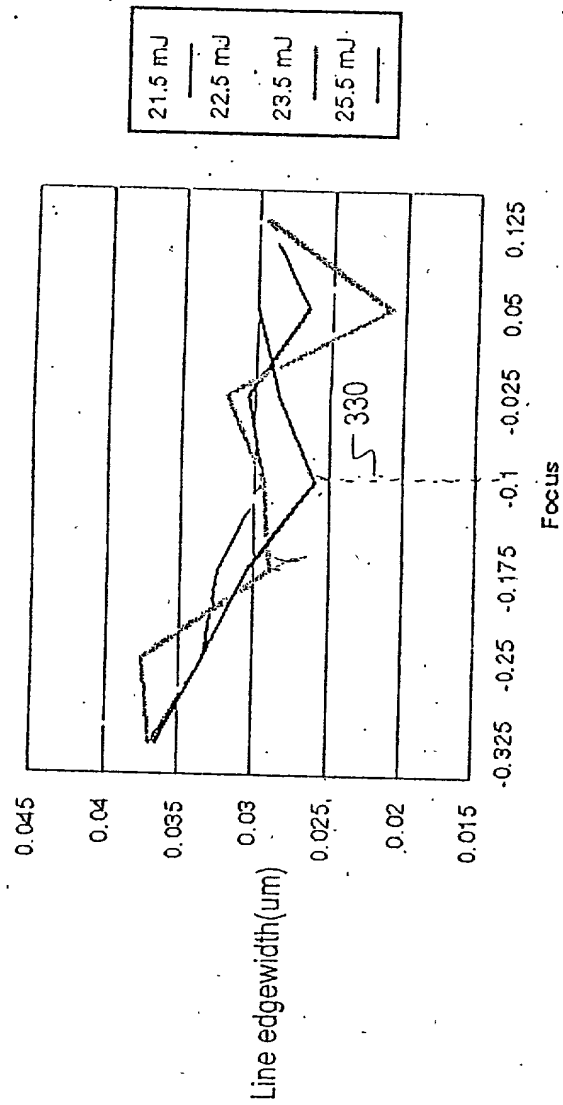


Fig 3

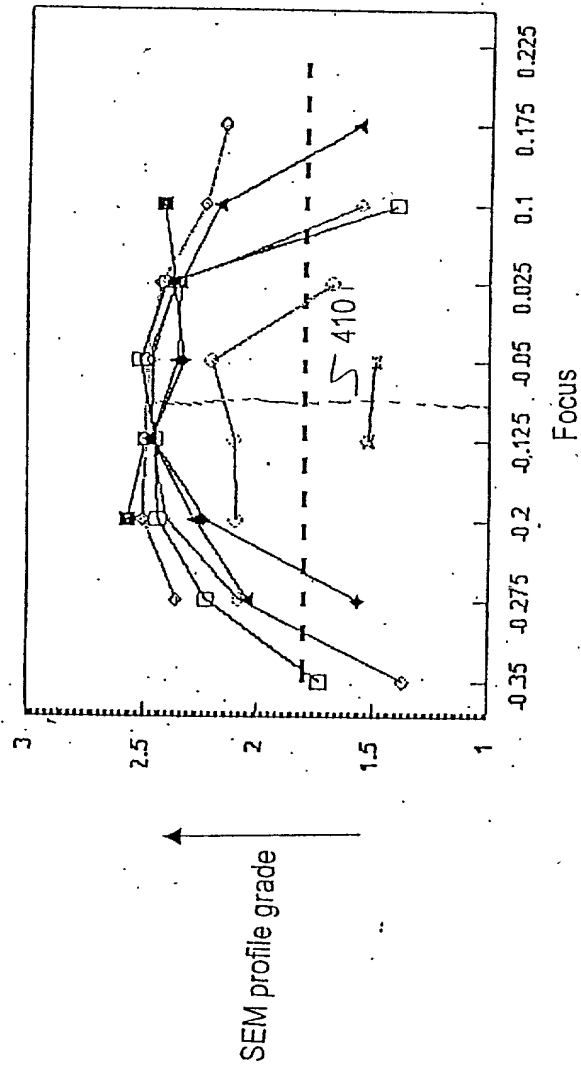


Fig. 4

Critical Dimension of Imaged Photoresist as Measured by CD

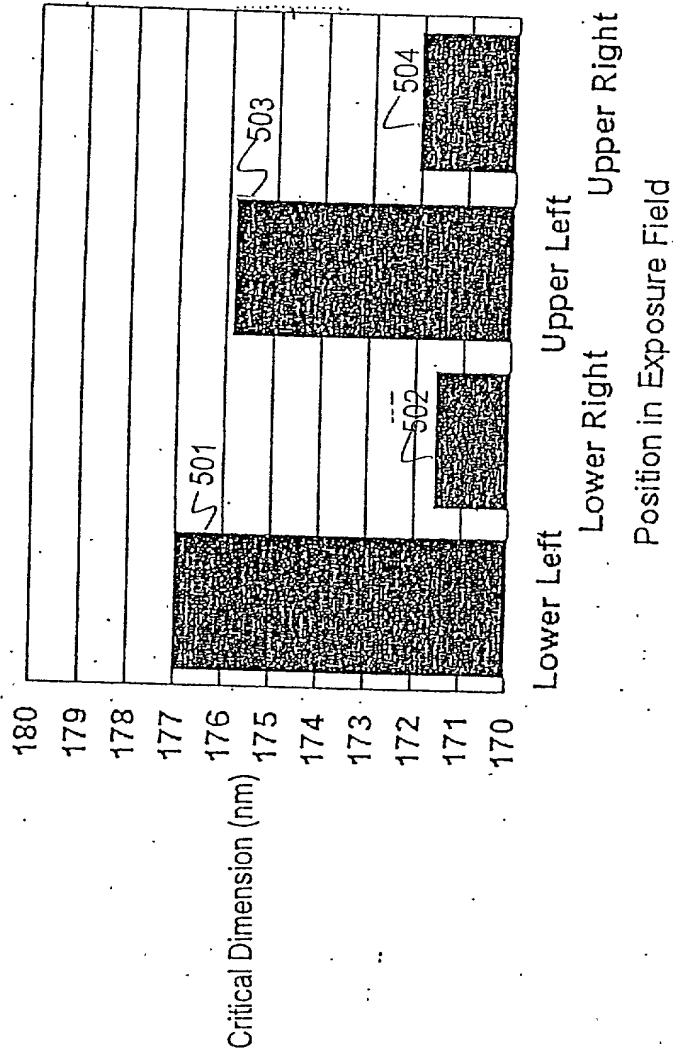


Fig. 5

Line Edge Width of Imaged Photoresist as Measured by CD

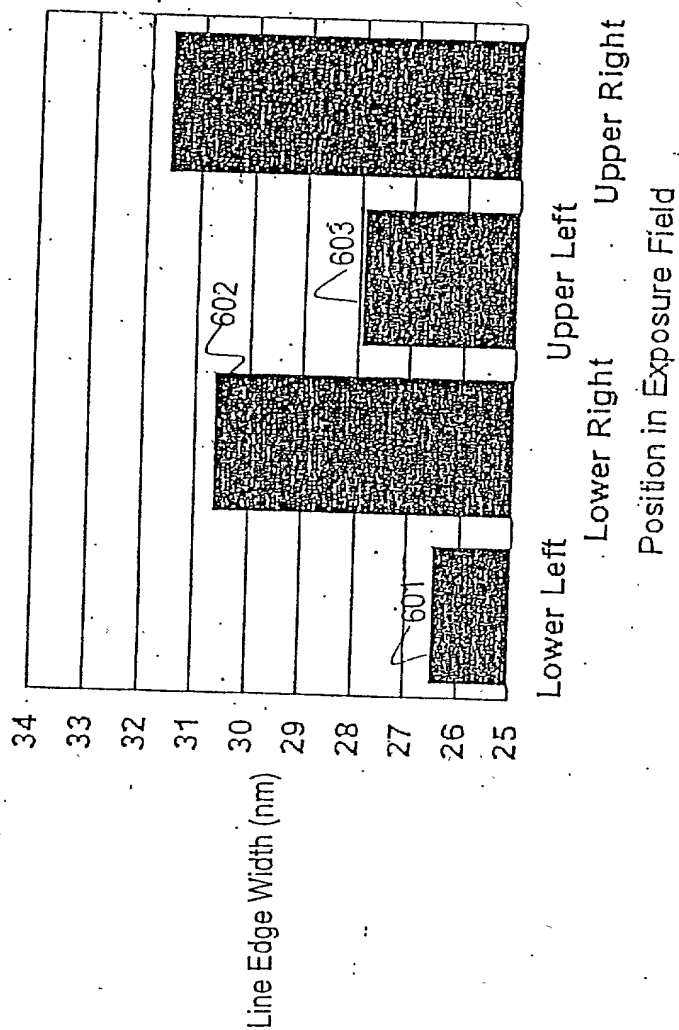


Fig. 6

X/Y Tilt Determination Using Edge Width Measurement

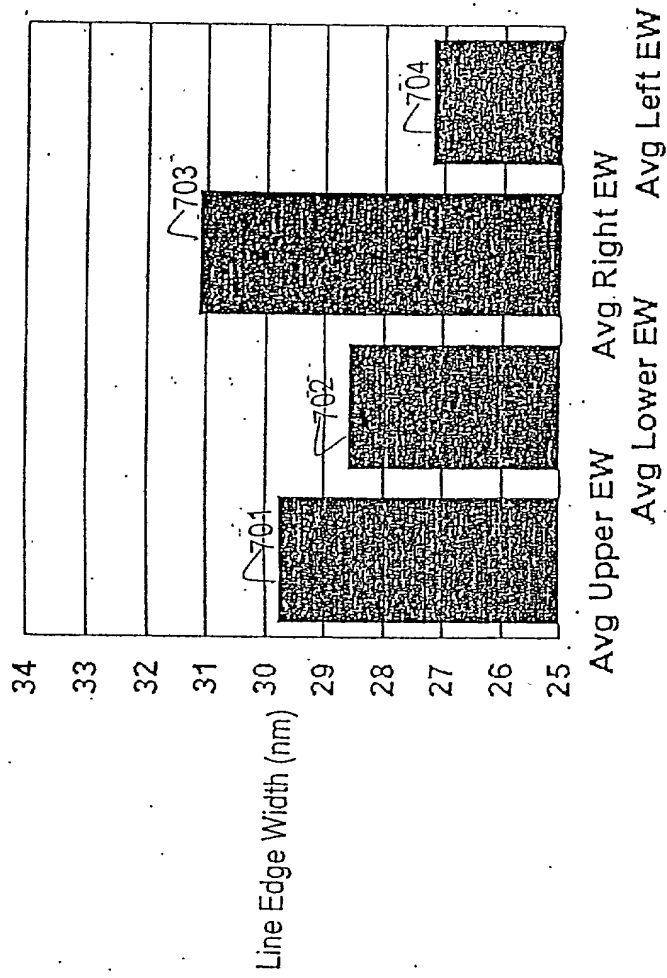


Fig. 7

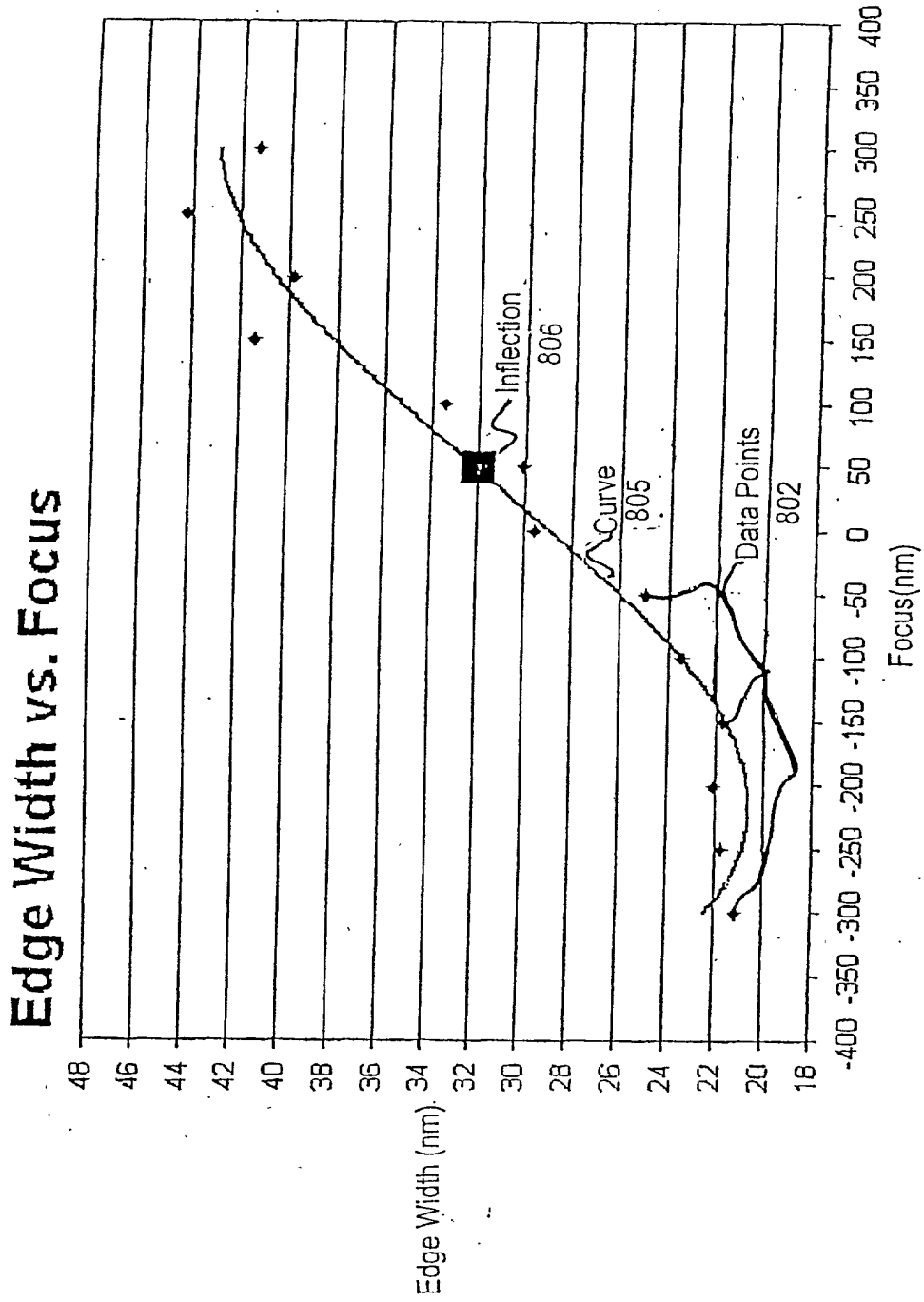


Fig. 8

XY Tilt Determination Using Edge Width Measurement

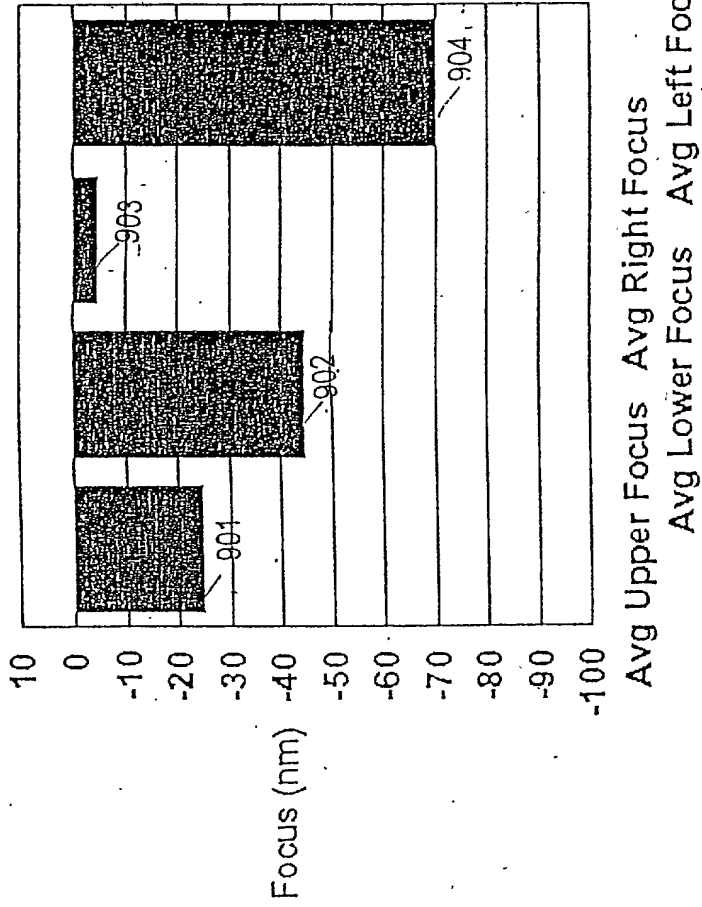


Fig. 9

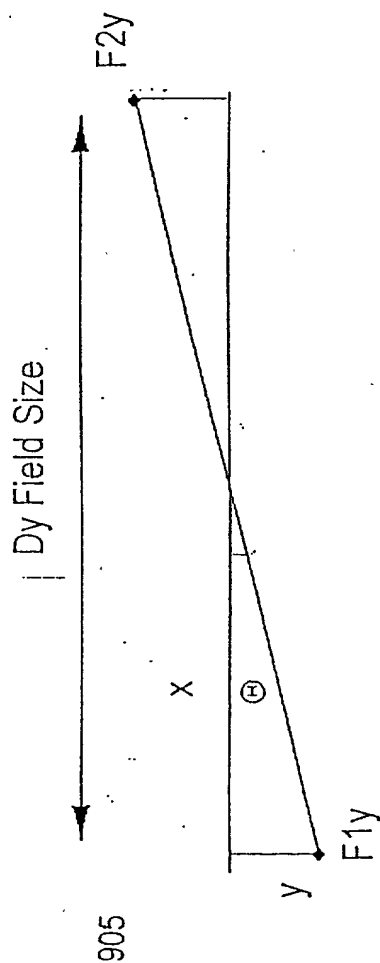


Fig. 10

Tool Check Center of Focus vs Atmospheric Press

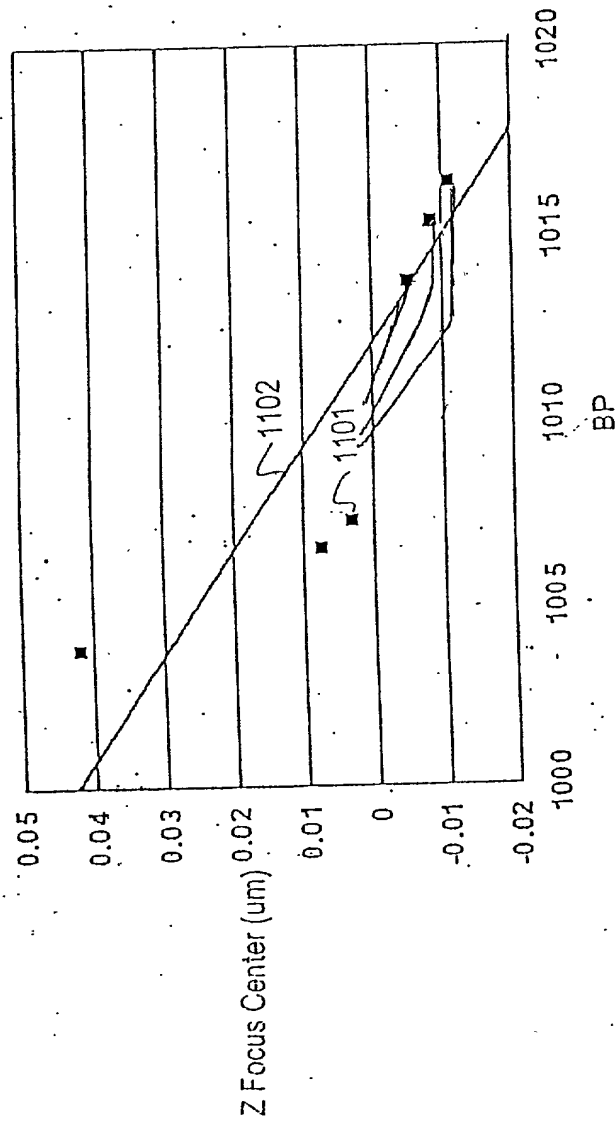


Fig. 11

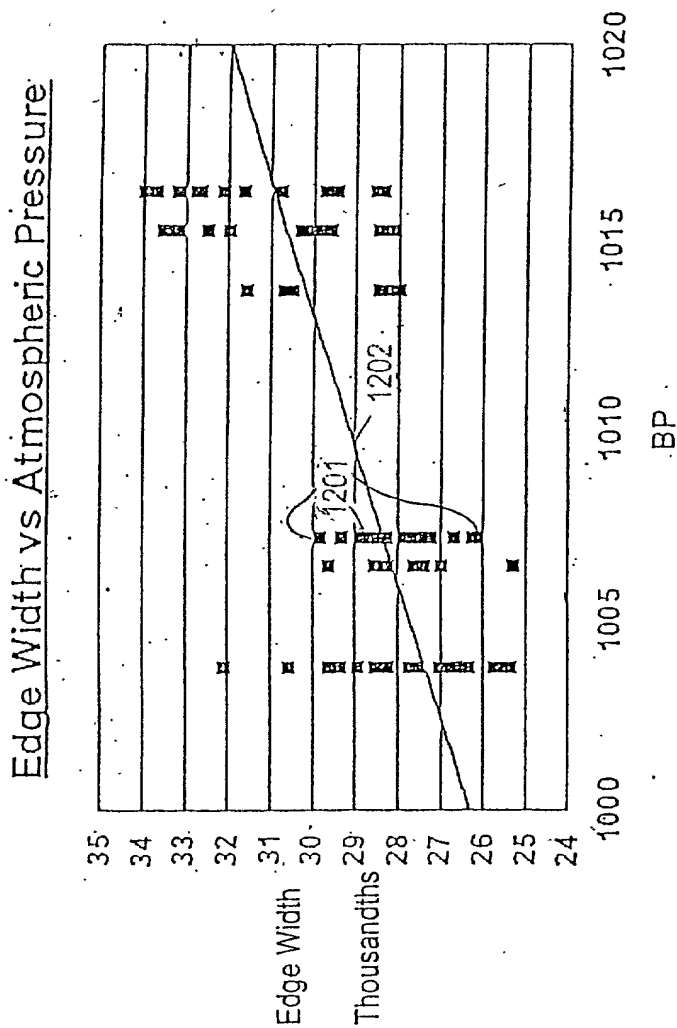


Fig. 12

TABLE OF RUN RULES

1310 Tool	1320 Technology	1330 WaferPN	1340 Process	1350 Opt	1360 Default Exposure	1370 Focus
U82V	ICE8S3D	*	MC	F	19.00	0.10
U82V	ICEC8S2	*	MC	F	19.00	0.10
U82V	ICEC8S3	*	MC	F	19.00	0.10
U84V	CMOS6X1	*	MC	F	20.00	0.00
U86V	CSOI9S0	*	MC9S	F	24.00	-0.10
U86V	CSOI9S0	0000008J0640	MC9S	F	30.00	-0.10
U86V	CSOI9S0	0000008J0645	MC9S	F	30.00	-0.10
U86V	CSOI9S0	0000057P6438	MC9S	F	28.00	-0.05
U86V	CSOI9S2	*	MC9S	F	25.00	-0.10
U92V	CSOI9S0	*	MC9S	F	24	-0.10
U92V	CSOI9S0	0000008J0639	MC9S	F	30.00	-0.10
U92V	CSOI9S0	0000008J0640	MC9S	F	30.00	-0.10

Fig. 13 (Prior Art)

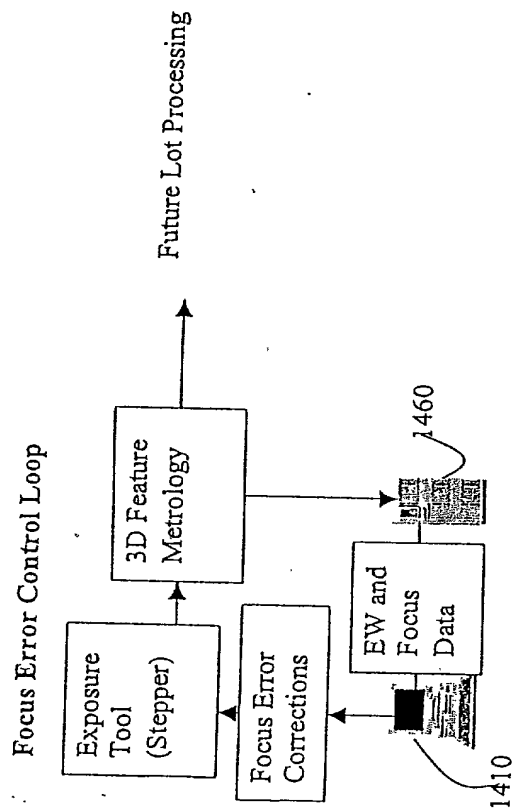


Fig. 14